Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package

2. Features and benefits

- Extremely fast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} \leq 78 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>		-	-	10	Α
Static characte	eristics						
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.4	1.8	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 6$		-	19	-	ns





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	$rac{1}{2}$	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package		Version			
	Name	Description	Version			
BYC10-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	T _{mb} ≤ 114 °C	-	500	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 78 °C; square-wave pulse; Fig. 1; Fig. 2	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; T _{mb} ≤ 78 °C; square-wave pulse	-	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	65	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	71	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

BYC10-600

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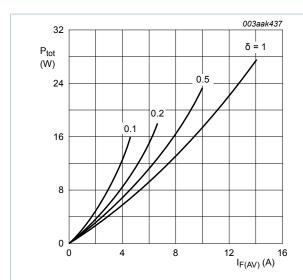


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

 $V_O = 1.300 \text{ V}; R_S = 0.050 \Omega$

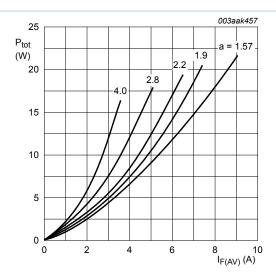


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

V_O = 1.300 V; R_S = 0.050 Ω

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

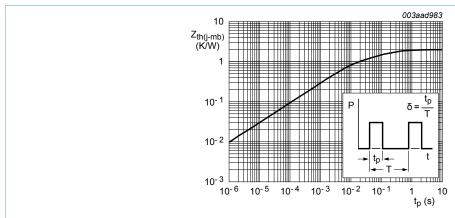


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	2	2.9	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.8	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.7	2.3	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C; <u>Fig. 5</u>	-	9	200	μA
		V _R = 500 V; T _j = 100 °C; <u>Fig. 5</u>	-	1.1	3	mA
Dynamic cl	haracteristics	-				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	35	55	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 6$	-	19	-	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ $\mu s; T_j = 100 \text{ °C}; Fig. 6$	-	32	40	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 6$	-	3	7.5	A
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 6$	-	9.5	12	A
V_{FRM}	forward recovery voltage	I_F = 10 A; dI_F/dt = 100 A/ μ s; T_j = 25 °C; Fig. 7	-	8	11	V

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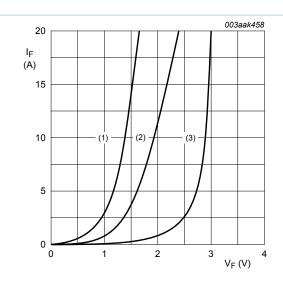


Fig. 4. Forward current as a function of forward voltage

(1)
$$T_j = 150$$
 °C; typical values;
(2) $T_j = 150$ °C; maximum values;
(3) $T_j = 25$ °C; maximum values;
 $V_O = 1.300$ V; $R_S = 0.050$ Ω

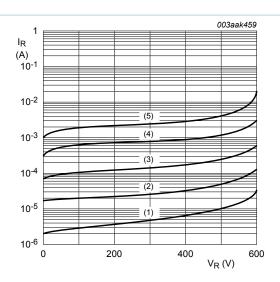


Fig. 5. Reverse leakage current as a function of reverse voltage; typical values

(1) $T_j = 25$ °C; typical values; (2) $T_j = 50$ °C; typical values; (3) $T_j = 75$ °C; typical values; (4) $T_j = 100$ °C; typical values; (5) $T_j = 125$ °C; typical value

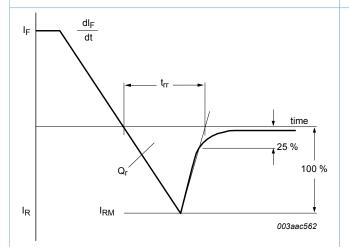


Fig. 6. Reverse recovery definitions; ramp recovery

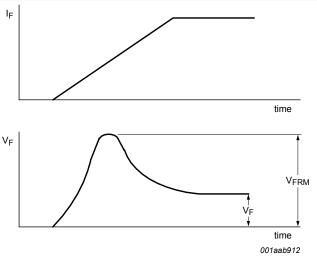
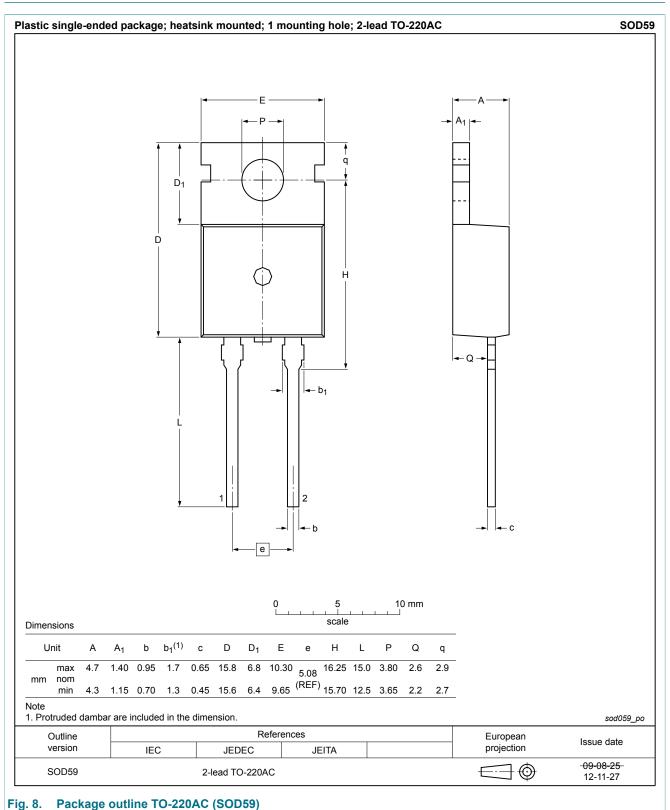


Fig. 7. Forward recovery definitions

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10. Package outline



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11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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